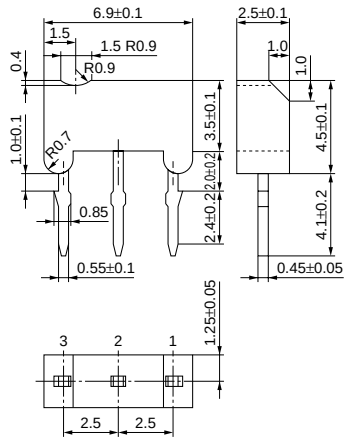
2SD973, 2SD973A

Silicon NPN epitaxial planer type

For low-frequency power amplification

Unit: mm



1:Base
2:Collector EIAJ:SC–71
3:Emitter M Type Mold Package

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings (Ta=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage	2SD973	V_{CBO}	30	V
	2SD973A		60	
Collector to emitter voltage	2SD973	V_{CEO}	25	V
	2SD973A		50	
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	1.5	A
Collector current		I_C	1	A
Collector power dissipation		P_C*	1	W
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 ~ +150	˚C

* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25˚C)

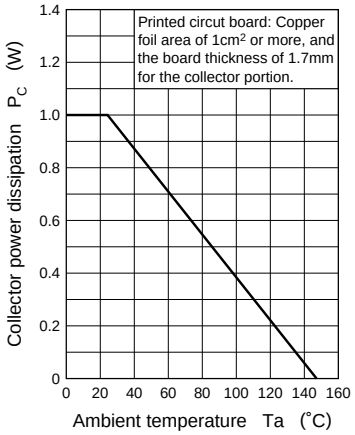
Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I_{CBO}	V_{CB} = 20V, I_E = 0			0.1	μA
Collector to base voltage	2SD973	V_{CBO}	I_C = 10μA, I_E = 0	30			V
	2SD973A			60			
Collector to emitter voltage	2SD973	V_{CEO}	I_C = 2mA, I_B = 0	25			V
	2SD973A			50			
Emitter to base voltage		V_{EBO}	I_E = 10μA, I_C = 0	5			V
Forward current transfer ratio		h_{FE1}*1	V_{CE} = 10V, I_C = 500mA*2	85	160	340	
		h_{FE2}	V_{CE} = 5V, I_C = 1A*2	50	100		
Collector to emitter saturation voltage		$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA*2		0.2	0.4	V
Base to emitter saturation voltage		$V_{BE(sat)}$	I_C = 500mA, I_B = 50mA*2		0.85	1.2	V
Transition frequency		f_T	V_{CB} = 10V, I_E = –50mA, f = 200MHz		200		MHz
Collector output capacitance		C_{ob}	V_{CB} = 10V, I_E = 0. f = 1MHz		11	20	pF

*2 Pulse measurement

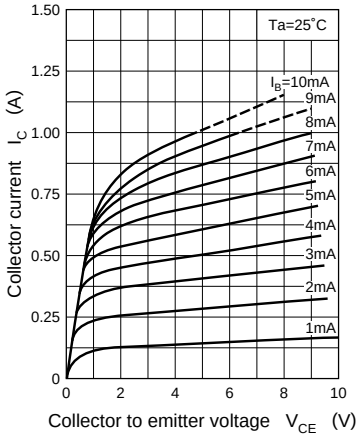
*1h_{FE1} Rank classification

Rank	Q	R	S
h_{FE1}	85 ~ 170	120 ~ 240	170 ~ 340

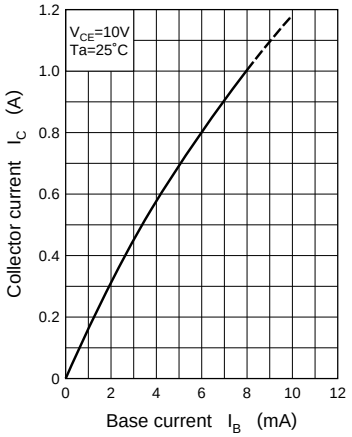
P_C — Ta



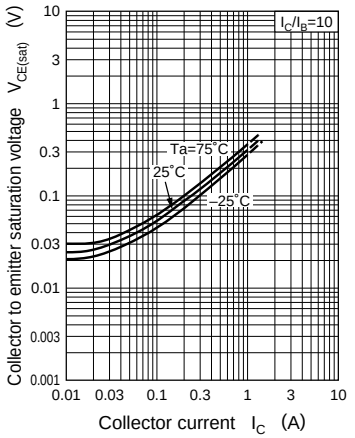
I_C — V_{CE}



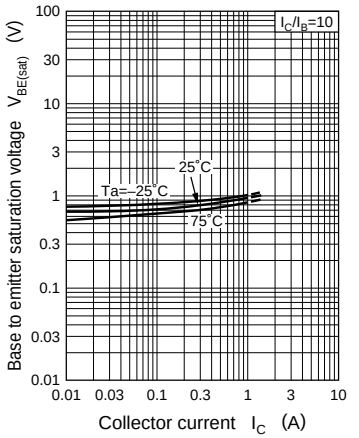
I_C — I_B



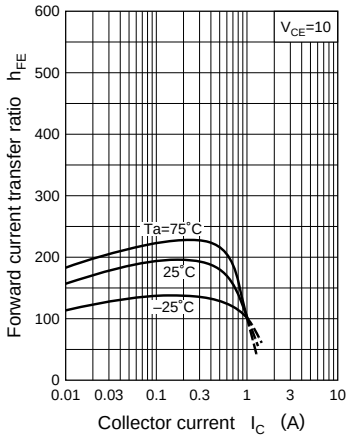
$V_{CE(sat)}$ — I_C



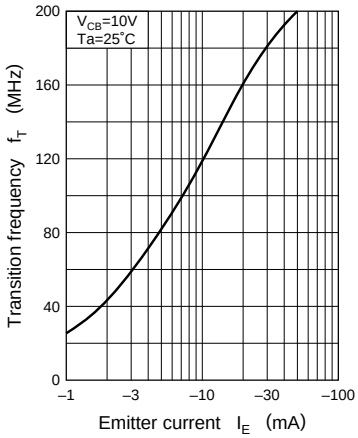
$V_{BE(sat)}$ — I_C



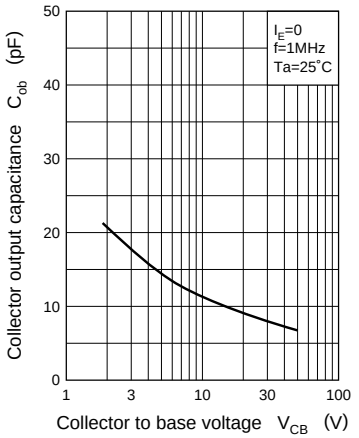
h_{FE} — I_C



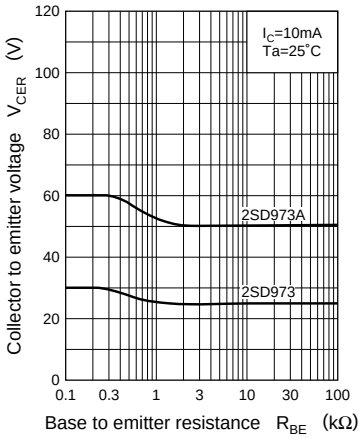
f_T — I_E



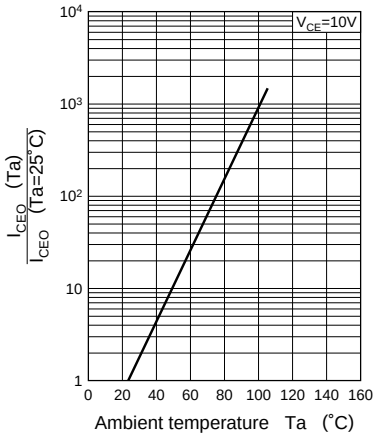
C_{ob} — V_{CB}



V_{CER} — R_{BE}



I_{CEO} — Ta



Area of safe operation (ASO)

